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*(Knowledge for Development)*

**KIBABII UNIVERSITY**

**2021/2022 ACADEMIC YEAR**

**UNIVERSITY EXAMINATIONS**

**SPECIAL/SUPPLEMENTARY EXAMINATIONS**

**YEAR ONE SEMESTER ONE EXAMINATIONS**

**FOR THE DEGREE OF**

**(COMPUTER SCIENCE)**

**COURSE CODE: CSC 113**

**COURSE TITLE: ELECTRONICS**

**DATE: 25/07/2022 TIME: 02.00 P.M. – 04.00 P.M.**

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**INSTRUCTIONS TO CANDIDATES**

**ANSWER QUESTION ONE AND ANY OTHER TWO (2) QUESTIONS**

### QUESTION ONE (COMPULSORY) [30 MARKS]

- a) Describe the phenomenon of avalanche and zener breakdown. [4mks]
- b) Draw the schematic of a pn-junction diode [2mks]
- (i) Forward-biased mode. [2mks]
- (ii) reverse-biased mode [2mks]
- Show in each case the polarity of voltage source (positive and negative terminal of the source) and the current direction.
- c) Can an ordinary diode be used as a zener diode? Justify your answer. [3mks]
- d) A load line intersects the forward V-I characteristic of a silicon diode at Q, where the slope of the curve is  $40\text{mA/V}$ . Calculate the diode resistance at the point Q. [4mks]
- e) With the help of a neat diagram, explain the operation of a Bridge Rectifier. What is PIV for the diode used here [10mks]
- f) What is intrinsic semiconductor? How do we make it extrinsic semiconductor, and why? [5mks]

### QUESTION TWO [20 MARKS]

- a) In the circuit diagram given, a volt meter is connected across a lamp, what changes would occur at lamp "L" and voltmeter "V", if the resistor R is reduced in value? Give reason(s) for your answer? [3mks]
- b) Draw the circuits to obtain the input and output characteristics of an NPN transistor in CE configuration. [10mks]
- c) With the aid of diagrams differentiate between CE, CB and CC configurations of BJT's. State the applications of each configuration [6mks]

### QUESTION THREE [20 MARKS]

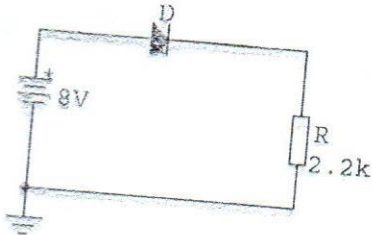
- a) Sketch the CE-configuration transistor output characteristics of a transistor and explain the significance of these curves. Indicate the active, cut-off and saturation regions. [10mks]
- b) State any FOUR differences between FET and BJT transistors. [4mks]
- c) Distinguish between majority and minority carriers in a semiconductor. Define mobility of charge carriers. [6mks]

**QUESTION FOUR [30 MARKS]**

- a) Discuss how a depletion layer is formed in a P-N junction and how does it vary with biasing? [12mks]  
Draw V-I characteristics of P-N junction diode.
- b) Explain the principle of operation of LED and outline the materials used for it. [8mks]

**QUESTION FIVE [30MKS]**

- a) Describe Zener diode and briefly explain how it regulates the voltage? What happens to the series current, load current and zener current when the d.c. input voltage of a zener regulator increases? [7mks]
- b) (i) For the series circuit shown determine  $V_D$ ,  $V_R$ , and  $I_D$ . [3mks]



- (ii) Suppose the diode in e(i) is reversed, determine  $V_D$ ,  $V_R$ , and  $I_D$ . [3mks]
- c) Explain the conduction of current in a good conductor. Why does a conductor have low resistance? [7mks]